

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor device comprising:
a plurality of semiconductor elements, each semiconductor element having first and second main electrodes and a control electrode;
a semiconductor substrate having a first principal ~~plane~~ surface on which the first and second main electrodes and the control ~~electrode~~ electrodes are located;
a film ~~over~~ at least partially covering the first main ~~electrode~~ electrodes and the control ~~electrode~~ electrodes, insulating the first main ~~electrode~~ electrodes and the control ~~electrode~~ electrodes from the second main ~~electrode~~ electrodes, and made of a polymer with a low dielectric constant; and
a chip surface electrode ~~over~~ at least partially covering the film ~~and~~, contacting the second main ~~electrode~~ electrodes, and connected to ground potential, wherein the second main ~~electrode~~ electrodes are provided with the ground potential through the chip surface electrode.

2. (Currently Amended) The semiconductor device according to claim 1, including a first pad connected to the first ~~electrode~~ main electrodes and a second pad connected to the ~~second electrode~~ control electrodes, the first and second pads being located on a ~~second principal plane, opposite the first principal plane~~ surface of the semiconductor ~~on which the electrodes are located~~ substrate.

3. (Previously Presented) The semiconductor device according to claim 1, wherein the semiconductor substrate is one of SiC and sapphire.

Claims 4-6 (Cancelled).

7. (New) The semiconductor device according to claim 1, including a heat sink on a second principal surface of the semiconductor substrate, opposite the first principal surface of the semiconductor substrate.

8. (New) The semiconductor device according to claim 7, wherein the heat sink is electrically conductive and is in electrical contact with the chip surface electrode.

9. (New) The semiconductor device according to claim 7, wherein the semiconductor substrate includes via holes electrically connecting respective first main electrodes to the heat sink.

10. (New) The semiconductor device according to claim 2, wherein the semiconductor substrate has a second principal surface opposite the first principal surface and side surfaces joining the first and second principal surfaces, and the first and second pads extend from the first principal surface to the second principal surface along the side surfaces of the semiconductor substrate.

11. (New) The semiconductor device according to claim 2, wherein the semiconductor substrate includes via holes electrically connecting the first pad to the heat sink.